

Silicon PNP Power Transistors

BDV64/64A/64B/64C

DESCRIPTION

- With TO-3PN package
- Complement to type BDV65/65A/65B/65C
- DARLINGTON
- High DC current gain

APPLICATIONS

- For use in general purpose amplifier applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

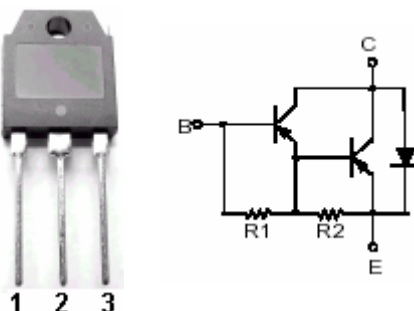


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BDV64	Open emitter	-60	V
		BDV64A		-80	
		BDV64B		-100	
		BDV64C		-120	
V_{CEO}	Collector-emitter voltage	BDV64	Open base	-60	V
		BDV64A		-80	
		BDV64B		-100	
		BDV64C		-120	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-12	A
I_{CM}	Collector current-peak			-15	A
I_B	Base current			-0.5	A
P_C	Collector power dissipation		$T_c=25^\circ\text{C}$	125	W
			$T_a=25^\circ\text{C}$	3.5	
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-65~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BDV64	I _C =-30mA, I _B =0	-60			V
		BDV64A		-80			
		BDV64B		-100			
		BDV64C		-120			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-5A, I _B =-20mA			-2.0	V
V _{BE}	Base-emitter on voltage		I _C =-5A; V _{CE} =-4V			-2.5	V
I _{CBO}	Collector cut-off current	BDV64	V _{CB} =-60V, I _E =0 V _{CB} =-30V, I _E =0; T _C =150°C			-0.4 -2.0	mA
		BDV64A	V _{CB} =-80V, I _E =0 V _{CB} =-40V, I _E =0; T _C =150°C			-0.4 -2.0	
		BDV64B	V _{CB} =-100V, I _E =0 V _{CB} =-50V, I _E =0; T _C =150°C			-0.4 -2.0	
		BDV64C	V _{CB} =-120V, I _E =0 V _{CB} =-60V, I _E =0; T _C =150°C			-0.4 -2.0	
I _{CEO}	Collector cut-off current	BDV64	V _{CE} =-30V, I _B =0			-2	mA
		BDV64A	V _{CE} =-40V, I _B =0				
		BDV64B	V _{CE} =-50V, I _B =0				
		BDV64C	V _{CE} =-60V, I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-5	mA
h _{FE}	DC current gain		I _C =-5A; V _{CE} =-4V	1000			
V _{EC}	Diode forward voltage		I _E =-10A			-3.5	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.0	°C/W

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PACKAGE OUTLINE

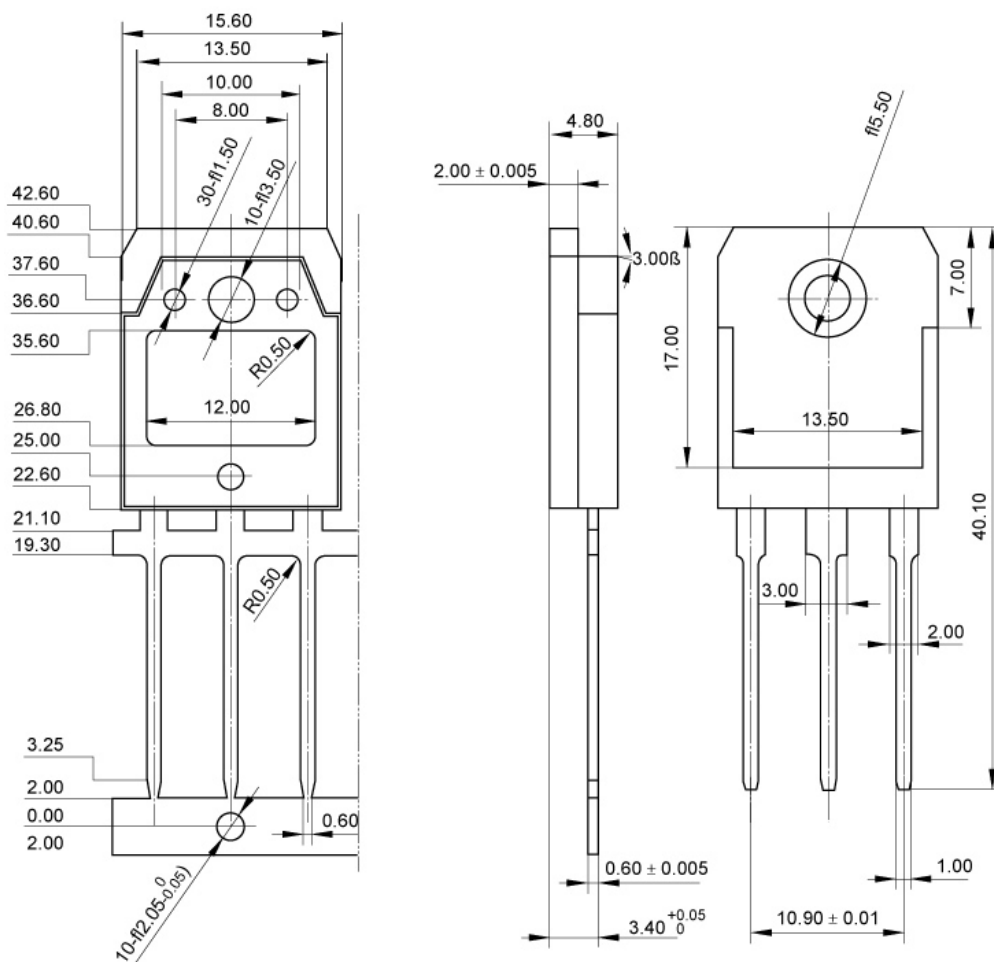


Fig.2 Outline dimensions(unindicated tolerance:±0.1mm)